

30V P-Channel MOSFET

- Features

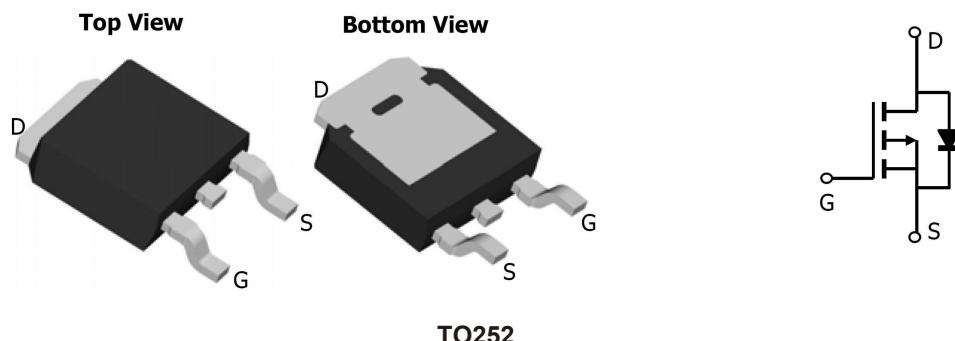
-30V70A ,
 $R_{DS(ON)} < 7.8m\Omega$ @ $V_{GS} = -10V$
 $R_{DS(ON)} < 11m\Omega$ @ $V_{GS} = -4.5V$
 Lead Free Available (RoHS Compliant)

- General Description

The FS70P03 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The FS70P03 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- Pin Configuration



- Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current, $V_{GS}@-10V^1$	I_D	-70	A
		-40	
		-11.3	
		-9	
Pulsed Drain Current ²	I_{DM}	-180	
Avalanche Current	I_{AS}	-55.4	
Single Pulse Avalanche Energy ³	E_{AS}	153	
Total Power Dissipation ⁴	P_D	2	
		52.1	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C
Thermal Characteristics			
Parameter	Symbol	Typ	Max
Maximum Junction-to-Ambient ¹	$R_{\theta JA}$	---	25
Maximum Junction-to-Ambient ¹		---	62
Maximum Junction-to-Case ¹		---	2.4

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- Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}, V_{GS}=0$	$T_J=25^\circ\text{C}$		-1	uA
			$T_J=25^\circ\text{C}$		-5	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 25\text{V}$			± 0.1	
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-1		-2.5	V
$R_{DS(\text{ON})}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10\text{V}, I_D=-30\text{A}$		6.8	7.8	mΩ
				9.0	11	
g_{FS}	Forward Trans conductance	$V_{DS}=-5\text{V}, I_D=-30\text{A}$		26.4		S
V_{SD}	Diode Forward Voltage ²	$I_S=1\text{A}, V_{GS}=0\text{V}, T_J=25^\circ\text{C}$			-1.2	V
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0\text{V}, \text{Force Current}$			-70	A
I_{SM}	Pulsed Source Current ^{2,5}				-190	
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-15\text{V}, f=1\text{MHz}$		3448		pF
C_{oss}	Output Capacitance			508		
C_{rss}	Reverse Transfer Capacitance			421		
SWITCHING PARAMETERS						
Q_g	Total Gate Charge(-4.5V)	$V_{GS}=-4.5\text{V}, V_{DS}=-15\text{V}, I_D=-15\text{A}$		33		nC
Q_{gs}	Gate Source Charge			10.7		
Q_{gd}	Gate Drain Charge			12.8		
$t_{D(\text{on})}$	Turn-On Delay Time	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, I_D=-15\text{A}, R_G=3.3\Omega$		8		ns
t_r	Turn-On Rise Time			17.8		
$t_{D(\text{off})}$	Turn-Off Delay Time			78.4		
t_f	Turn-Off Fall Time			43.6		
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-15\text{A}, dI/dt=100\text{A}/\mu\text{s}, T_J=25^\circ\text{C}$		29		
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-15\text{A}, dI/dt=100\text{A}/\mu\text{s}, T_J=25^\circ\text{C}$		15		nC

Note:

A: Th1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$

3.The EAS data shows Max. rating . The test condition is $VDD=-25\text{V}, VGS=-10\text{V}, L=0.1\text{mH}, IAS=-55.4\text{A}$

4.The power dissipation is limited by 150°C junction temperature

5.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

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- TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

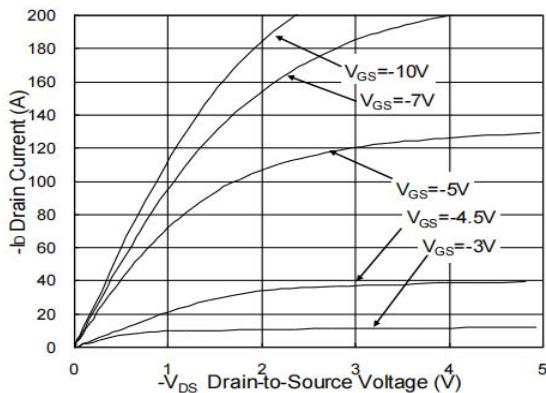


Fig.1 Typical Output Characteristics

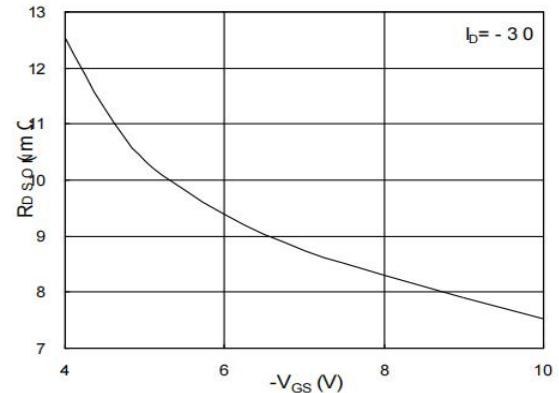


Fig.2 On-Resistance v.s Gate-Source

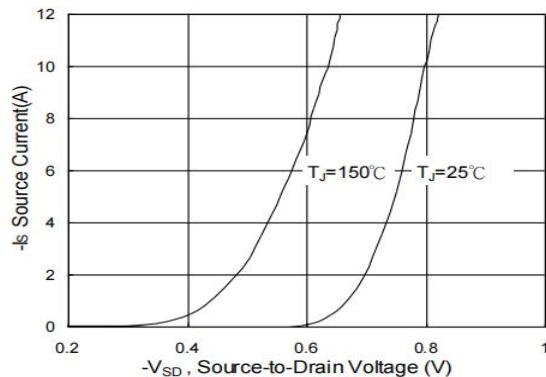


Fig.3 Forward Characteristics Of Reverse

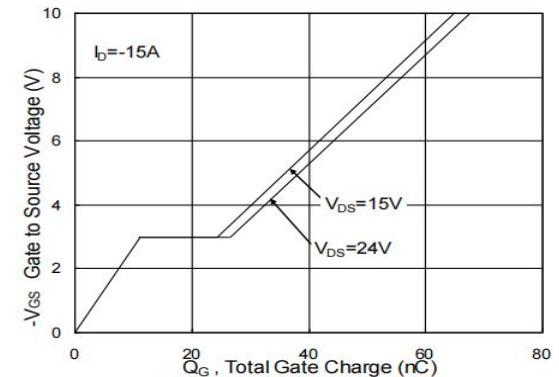


Fig.4 Gate-Charge Characteristics

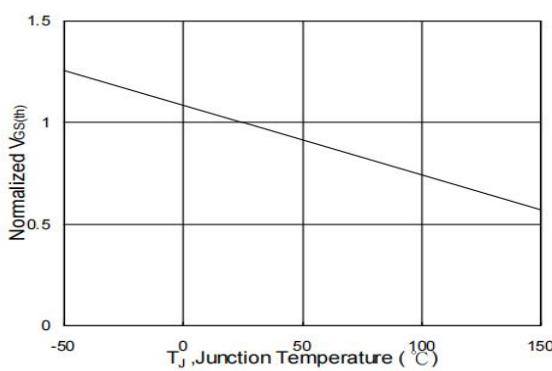


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

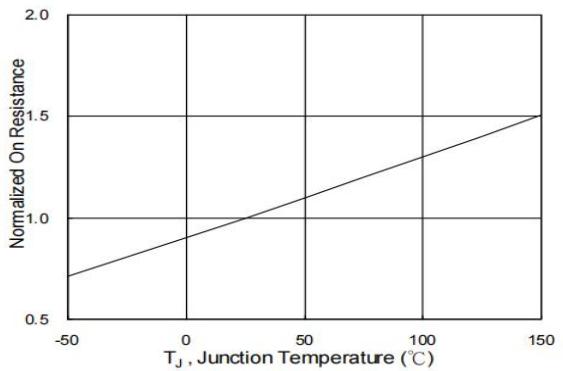


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

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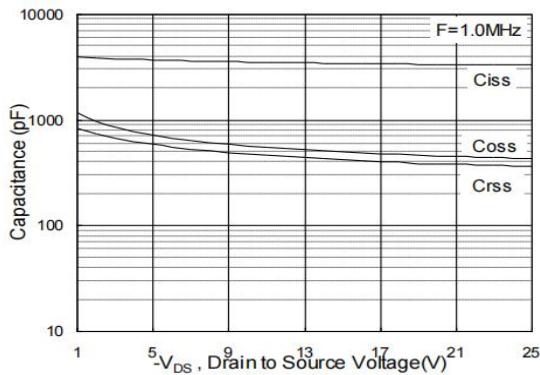


Fig.7 Capacitance

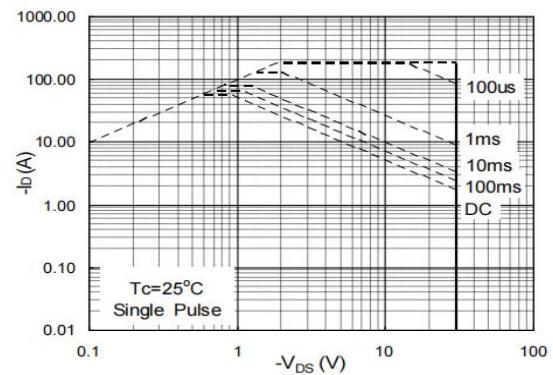


Fig.8 Safe Operating Area

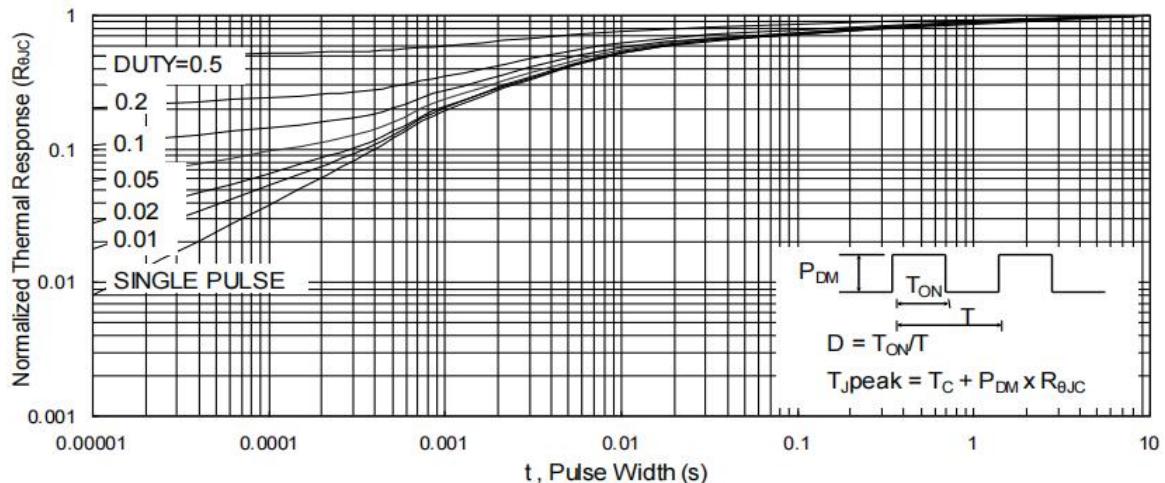


Fig.9 Normalized Maximum Transient Thermal Impedance

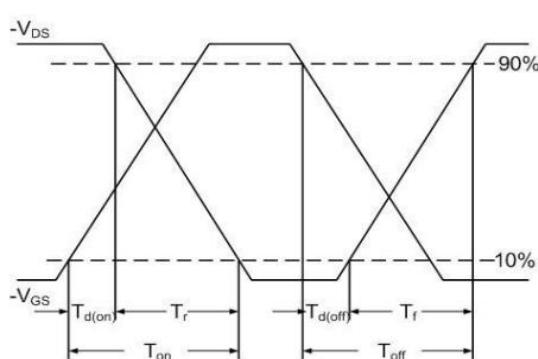


Fig.10 Switching Time Waveform

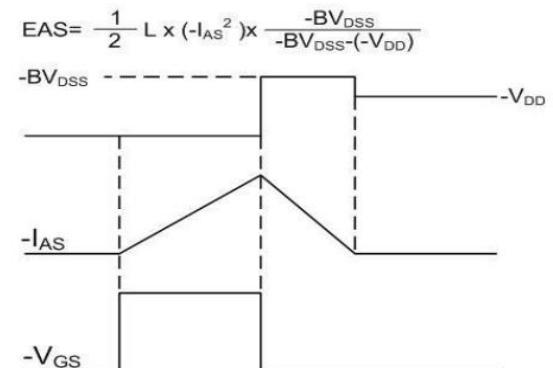
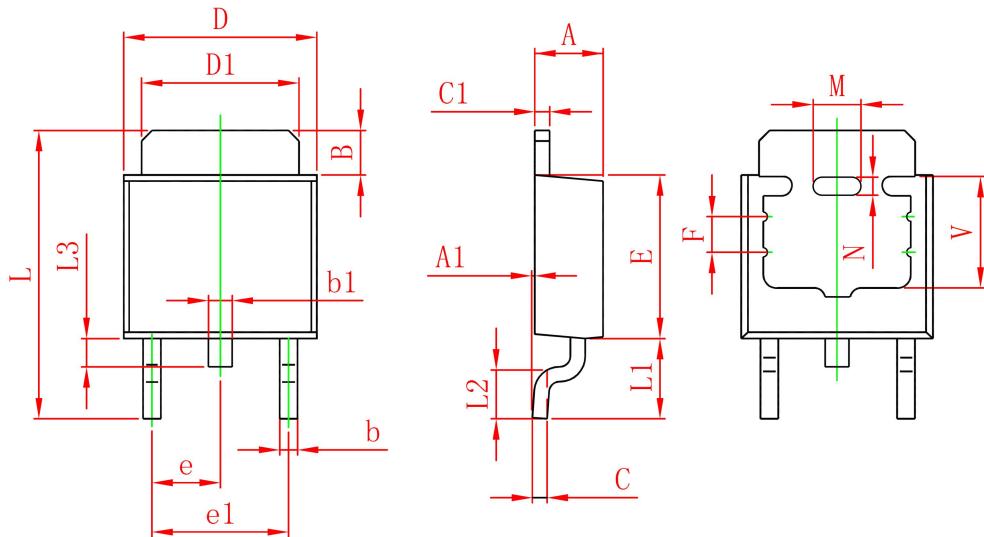


Fig.11 Unclamped Inductive Switching Waveform

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● Package Information

TO-252C-2L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
F	1.200REF.		0.047REF.	
M	1.600REF.		0.063REF.	
N	0.450REF.		0.018REF.	
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF		0.150 REF	